Gamma irradiation of ITk silicon strip modules with early breakdown LHCP 2024: 12th Edition of the Large Hadron Collider Physics Conference Boston, Massachusetts — 3-7 June 2024





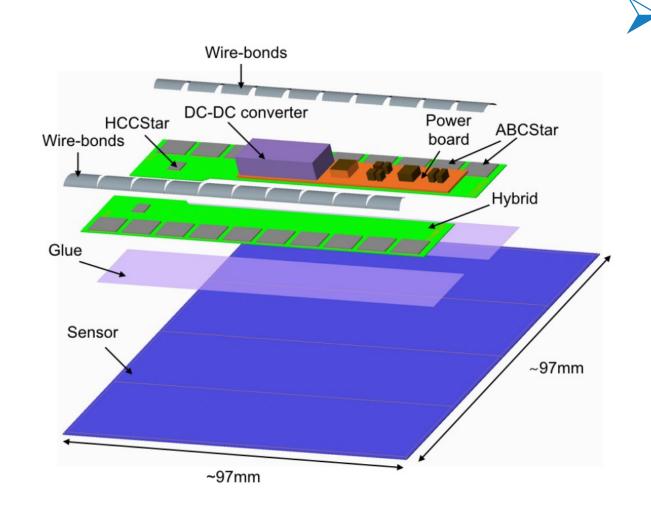
1. Early breakdown in silicon strip modules

- ITk silicon strip sensors consist of a silicon sensor, hybrids (host readout electronics),
- Sensors require -500V bias voltage for operation
- Early breakdown observed during module assembly due to
 - Mechanical damage (chips,

2. Gamma irradiation to cure early breakdown

- Sensors irradiated by Prague group showed early breakdown cured by 11 krad of gamma radiation [3]
 - > Will we get the same effect after gluing?
- Similar ionizing irradiation can be performed at BNL gamma facility with ⁶⁰Co source

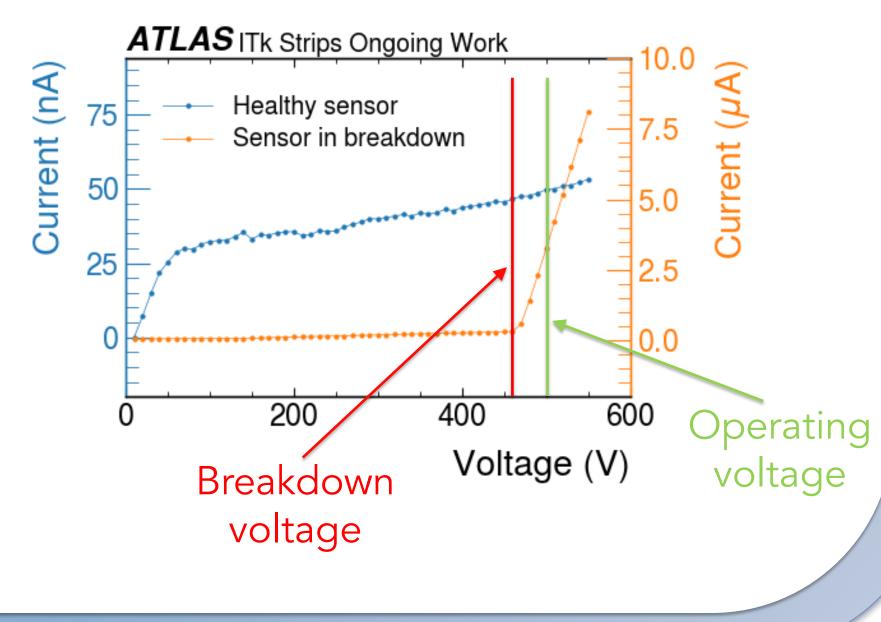
and a power board (power, monitor, and control electronics)



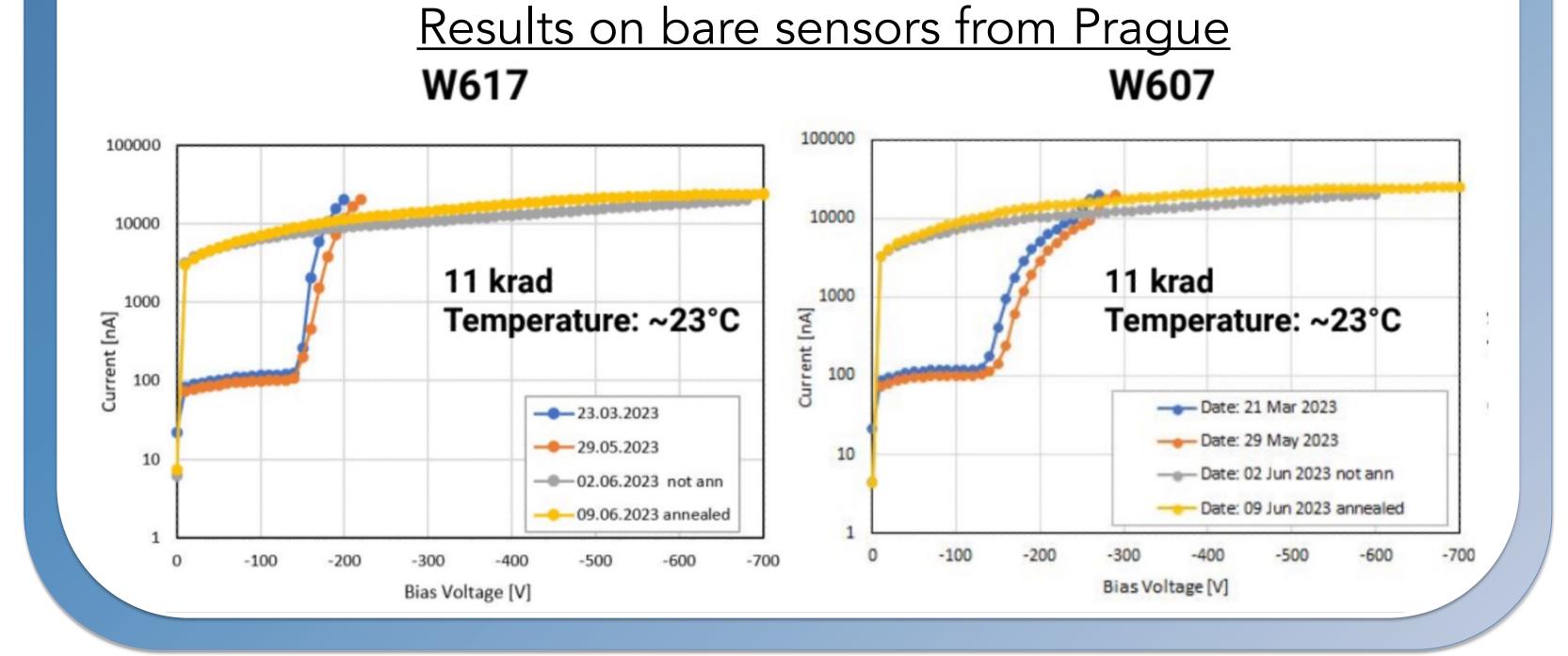
Expanded view of ITk short-strip barrel module [1]

cracks, scratches)

- > Static charge
- Long-term application of bias voltage
- \succ Glue on the guard ring [2]
- Can we reliably recover these modules?

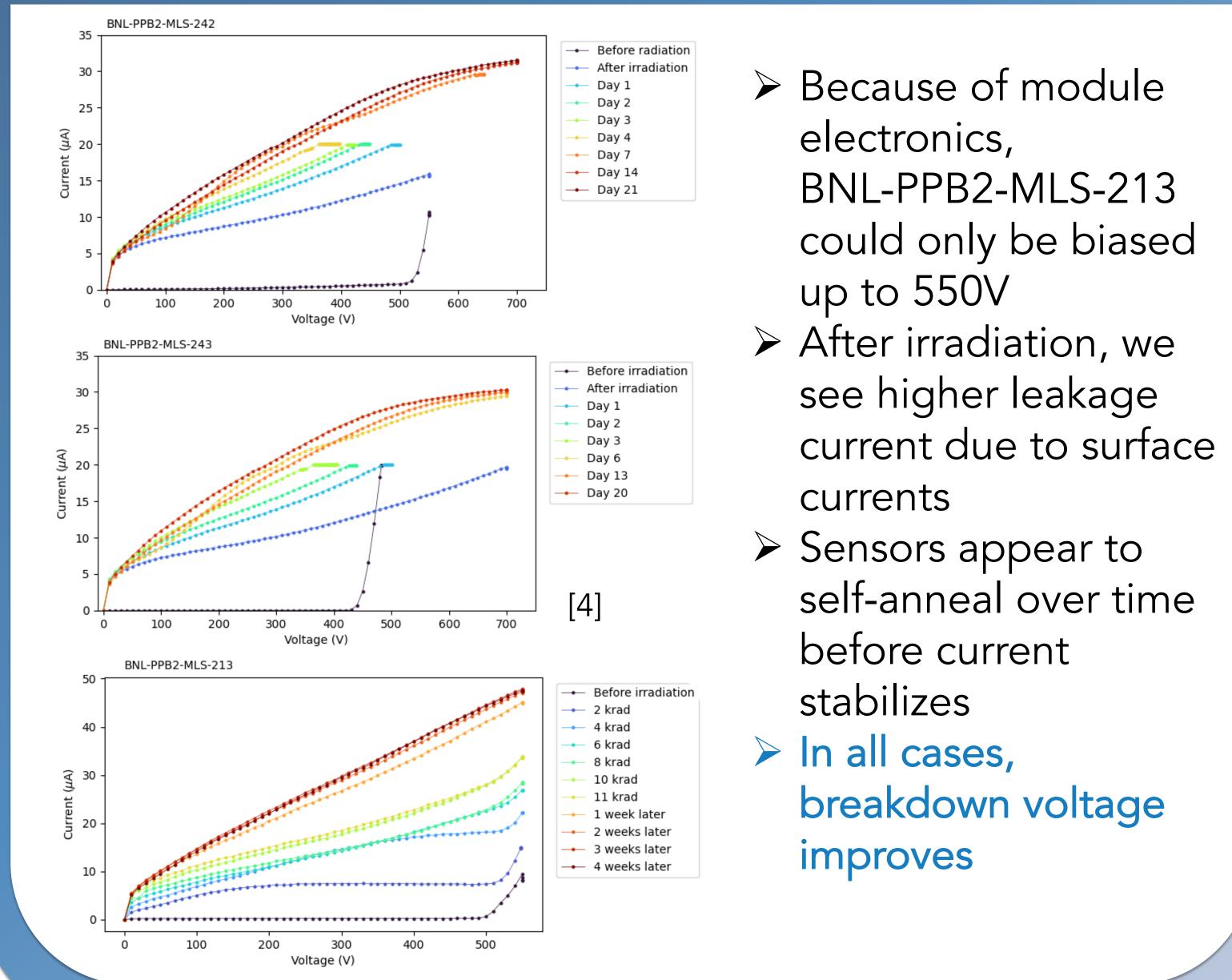


> We irradiated modules with 11krad of ionizing radiation at BNL, equivalent to 1 week in HL-LHC

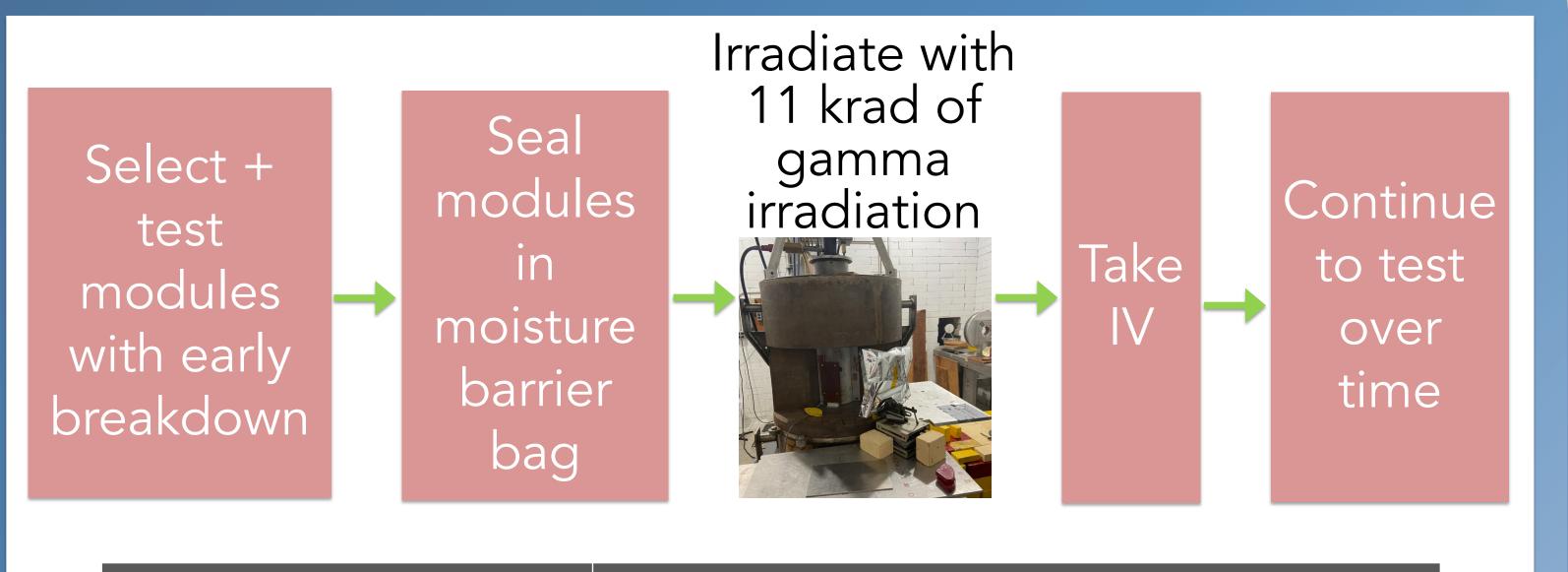


4. Results

5. Future work



3. Irradiation procedure



Irradiated module Special characteristics BNL-PPB2-MLS-242 Breakdown ~520V, unbonded BNL-PPB2-MLS-243 Breakdown ~450V, unbonded BNL-PPB2-MLS-213 Breakdown ~500V, glue on the guard ring



BNL-PPB2-MLS-242

> Two unbonded modules developed early breakdown after gluing the hybrid onto the sensor Irradiated before continuing assembly > One module with glue on the guard ring irradiated (known cause of early breakdown [2])

> 11krad of ionizing radiation cured early breakdown in 3 modules, 1 with glue on the guard ring

- > Modules will experience this dose in just 1 week of HL-LHC
- BNL plans to irradiate more modules with early breakdown as they are discovered, particularly modules with glue on the guard ring
- These results mark a significant step towards establishing a reliable pattern of component recovery during detector operation

6. References

[1] Technical Design Report for the ATLAS Inner Tracker Strip Detector. Technical Report CERN-LHCC-2017-005. ATLAS-TDR-025, CERN, Geneva, Apr 2017.

[2] C. Helling, L. Poley et al. Study of n-on-p sensors breakdown in presence of dielectrics placed on top surface, NIMA, Volume 924, 21 April 2019, Pages 147-152

[3] M. Mikestikova, et al. Gamma irradiation of ATLAS18 ITk strip sensors affected by static charge, Proceedings of Science, VERTEX2023 (2024) 026 [4] Luise Poley et al. Curing early breakdown in silicon strip sensors with radiation, NIMA, Volume 1064 (2024,)169405



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